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501.39868X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): T. SAITO et al  
Serial No.: 09/850,162  
Filed: May 8, 2001  
For: A SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE  
AND A METHOD OF MANUFACTURING THE SAME  
Group: 2812  
Examiner: R. E. POMPEY

SUPPLEMENTING AMENDMENT

Assistant Commissioner of Patents  
Washington, D. C. 20231

Sept. 12, 2002

Sir:

Further to the fully responsive Amendment filed on September 3, 2002, the following additional amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE SUBSTITUTE SPECIFICATION:

Please replace paragraph [0064] as follows:

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[0064] Subsequently, as shown in Fig. 1b, the semiconductor substrate 1 is cleaned on the surface thereof by wet etching using, for example, hydrofluoric acid, and it is subsequently thermally oxidized at about 800 to 850°C to form a clean gate oxide film 5 having a thickness of approximately 7nm on the surface thereof.

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